International Rectifier

HFA16PA60C

HEXFRED™

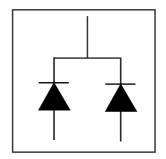
Ultrafast, Soft Recovery Diode

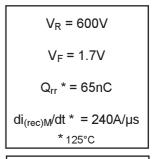
Features

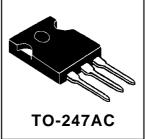
- · Ultrafast Recovery
- · Ultrasoft Recovery
- Very Low I_{RRM}
- Very Low Q_{rr}
- · Guaranteed Avalanche
- · Specified at Operating Conditions

Benefits

- Reduced RFI and EMI
- Reduced Power Loss in Diode and Switching Transistor
- · Higher Frequency Operation
- · Reduced Snubbing
- · Reduced Parts Count







Description

International Rectifier's HFA16PA60C is a state of the art center tap ultra fast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 volts and 8 amps per Leg continuous current, the HFA16PA60C is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultra fast recovery time, the HEXFRED product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA16PA60C is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

Absolute Maximum Ratings (per Leg)

	Parameter	Max.	Units
VR	Cathode-to-Anode Voltage	600	V
I _F @ T _C = 25°C	Continuous Forward Current		
I _F @ T _C = 100°C	Continuous Forward Current (per Leg)	8]
I _{FSM}	Single Pulse Forward Current	60	Α
I _{FRM}	Maximum Repetitive Forward Current	24	
I _{AR} ①	Maximum Repetitive Avalanche Current	0.5	
P _D @ T _C = 25°C	Maximum Power Dissipation	36	
P _D @ T _C = 100°C	Maximum Power Dissipation	14	_ w
TJ	Operating Junction and	FF + 14F0	°C
T _{STG}	Storage Temperature Range	-55 to +150	

Electrical Characteristics (per Leg) @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Test Conditions	
V_{BR}	Cathode Anode Breakdown Voltage	600			V	I _R = 100μA	
V _{FM}	Max Forward Voltage		1.4	1.7	V	I _F = 8A	
			1.7	2.1		I _F = 16A See Fig. 1	
			1.4	1.7		I _F = 8A, T _J = 125°C	
I _{RM}	Max Reverse Leakage Current		0.3	5	μA	$V_R = V_R$ Rated See Fig. 2	
			100	500	μA	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ Rated	
C _T	Junction Capacitance		10	25	pF	V _R = 200V See Fig. 3	
L _S	Series Inductance		8.0		- nH	Measured lead to lead 5mm from	
						package body	

Dynamic Recovery Characteristics (per Leg) @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Test Conditions		
t _{rr}	Reverse Recovery Time		18			$I_F = 1.0A$, $di_f/dt = 200A/\mu s$, $V_R = 30V$		
t _{rr1}	See Fig. 5, 6 & 16		37	55	ns	T _J = 25°C		
t _{rr2}			55	90		T _J = 125°C	I _F = 8A	
I _{RRM1}	Peak Recovery Current		3.5	5.0	Α	T _J = 25°C		
I _{RRM2}	See Fig. 7& 8		4.5	8.0		T _J = 125°C	V _R = 200V	
Q _{rr1}	Reverse Recovery Charge		65	138	nC	T _J = 25°C		
Q _{rr2}	See Fig. 9 & 10		124	360	IIC	T _J = 125°C	$di_f/dt = 200A/\mu s$	
di _{(rec)M} /dt1	Peak Rate of Fall of Recovery Current		240		A/µs	T _J = 25°C		
di _{(rec)M} /dt2	During t _b See Fig. 11 & 12		210		Α/µS	T _J = 125°C		

Thermal - Mechanical Characteristics

	Parameter	Min.	Тур.	Max.	Units	
T _{lead} ②	Lead Temperature			300	°C	
R _θ JC	Junction-to-Case, Single Leg Conducting			3.5		
	Junction-to-Case, Both Legs Conducting			1.75	_{K/W}	
R _{0JA} ③	Thermal Resistance, Junction to Ambient			40	1000	
R _{0CS}	Thermal Resistance, Case to Heat Sink		0.25			
Wt	Weight		6		g	
			0.21		(oz)	
	Mounting Torque	6		12	Kg-cm	
		5		10	lbf•in	

- \odot $\;$ L=100 $\mu H,$ duty cycle limited by max T_J
- ② 0.063 in. from Case (1.6mm) for 10 sec
- 3 Typical Socket Mount
- Mounting Surface, Flat, Smooth and Greased

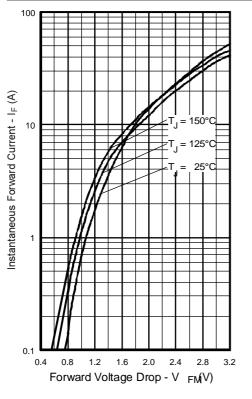


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current, (per Leg)

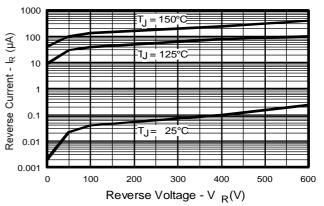


Fig. 2 - Typical Reverse Current vs. Reverse Voltage, (per Leg)

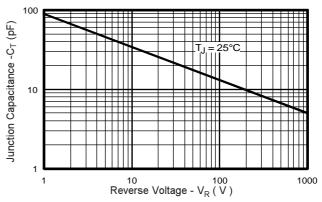
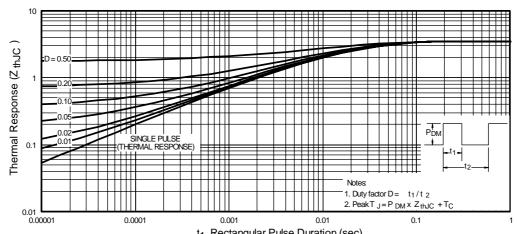


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage, (per Leg)



 $t_{1}, \text{Rectangular Pulse Duration (sec)} \\ \textbf{Fig. 4 - Maximum Thermal Impedance } Z_{thjc} \textbf{ Characteristics, (per Leg)} \\$

HFA16PA60C

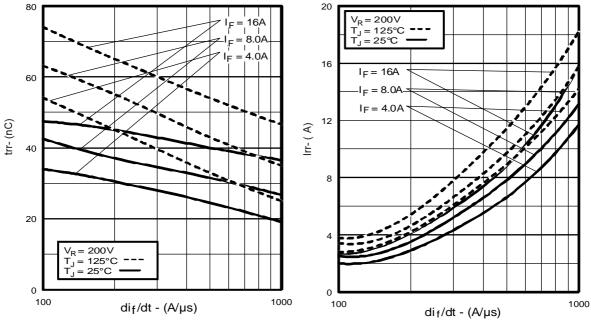
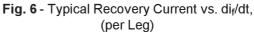


Fig. 5 - Typical Reverse Recovery vs. di_f/dt, (per Leg)



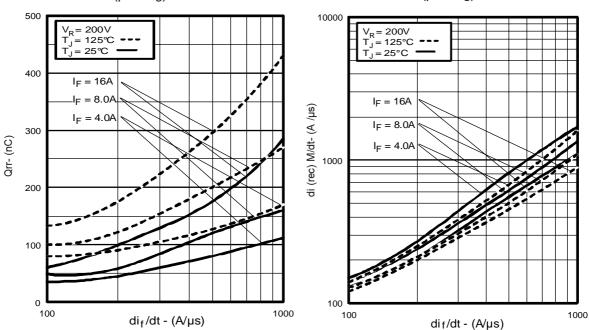


Fig. 7 - Typical Stored Charge vs. di_f/dt, (per Leg)

Fig. 8 - Typical $di_{(rec)M}/dt$ vs. di_f/dt , (per Leg)

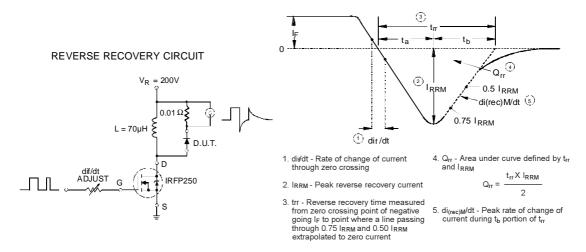


Fig. 9 - Reverse Recovery Parameter Test Circuit

Fig. 10 - Reverse Recovery Waveform and Definitions

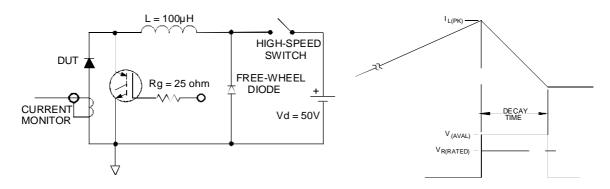
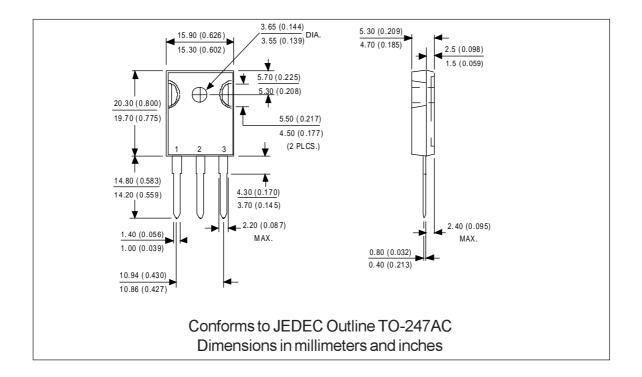


Fig. 11 - Avalanche Test Circuit and Waveforms



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